<u> </u>			Me
Notice of Allowability	Application No.	Applicant(s)	
	10/667,013	TSAI ET AL.	
	Examiner	Art Unit	
	Luan Thai	2829	
The MAILING DATE of this communication at All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATEN of the Office or upon petition by the applicant. See 37 CFR 1	S IS (OR REMAINS) CLOSED in85) or other appropriate comm <b>T RIGHTS</b> . This application is	n this application. If not include unication will be mailed in due	ed course. <b>THIS</b>
1. This communication is responsive to			
2. ☑ The allowed claim(s) is/are <u>1-26</u> .			
3. X The drawings filed on 19 September 2003 are accepte	d by the Examiner.		
<ul> <li>4. Acknowledgment is made of a claim for foreign priorit</li> <li>a) All</li> <li>b) Some*</li> <li>c) None</li> <li>d the:</li> <li>1. Certified copies of the priority documents I</li> <li>2. Certified copies of the priority documents I</li> </ul>	nave been received.		
Copies of the certified copies of the priority	• •		tion from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DA' noted below. Failure to timely comply will result in ABANDO THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the red	quirements
5. A SUBSTITUTE OATH OR DECLARATION must be so INFORMAL PATENT APPLICATION (PTO-152) which	ubmitted. Note the attached EX gives reason(s) why the oath o	AMINER'S AMENDMENT or N r declaration is deficient.	OTICE OF
6. CORRECTED DRAWINGS ( as "replacement sheets")	must be submitted.		
(a)  including changes required by the Notice of Drafts	person's Patent Drawing Revie	w ( PTO-948) attached	
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date		•	
<ul><li>(b) ☐ including changes required by the attached Exami Paper No./Mail Date</li></ul>	ner's Amendment / Comment o	r in the Office action of	
Identifying indicia such as the application number (see 37 Cleach sheet. Replacement sheet(s) should be labeled as such	FR 1.84(c)) should be written on t in the header according to 37 C	he drawings in the front (not the FR 1.121(d).	back) of
<ol> <li>DEPOSIT OF and/or INFORMATION about the deattached Examiner's comment regarding REQUIREME</li> </ol>	eposit of BIOLOGICAL MAT NT FOR THE DEPOSIT OF BI	ERIAL must be submitted. NOLOGICAL MATERIAL.	Note the
			•
Attachment(s)	6 <b></b>		
<ol> <li>Notice of References Cited (PTO-892)</li> <li>D Notice of Draftperson's Patent Drawing Review (PTO-94</li> </ol>		nformal Patent Application (PTC	J-152)
	Paper No.	Summary (PTO-413), /Mail Date	
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/5 Paper No./Mail Date 2/3/04&amp;3/19/04</li> </ol>	SB/08), 7.   Examiner's	: Amendment/Comment	
4. Examiner's Comment Regarding Requirement for Depo		Statement of Reasons for Allo	wance
of Biological Material	9. ☐ Other		
Chaile LUANT PRIMARY EX	Hai 12/9/04 Kaminer	1	

## **DETAILED ACTION**

1. Claims 1-26 are allowed.

2. The following is an examiner's statement of reasons for allowance:

The cited art taken either singly or in combination with other prior arts fails to anticipate or fairly suggest the limitations which the Applicant claims in a manner which would warrant a rejection under 35 U.S.C. § 102 or 35 U.S.C. § 103, especially when these limitations are considered within the specific combination claimed.

The cited art, U.S. Pat. No. 5,286,344 to Blalock et al., discloses a method for forming an opening in a multiplayer structure. Blalock et al., however, fails to teach or fairly suggest, among others, at least the method steps of: a) performing a plasma treatment on the photoresist layer using a nitrogen-based gas; and performing a wet strip to remove the patterned photoresist layer, as claimed in claim 1; b) performing a plasma treatment on the exposed portion of the stop layer, removing at least the exposed portion of the stop layer to expose a portion of the metal silicide layer, depositing a barrier layer over the exposed portion of the metal silicide layer, and planarizing any layers above the ILD layer to expose the ILD layer, as claimed in claim 5; c) performing a plasma treatment on the exposed portion of the middle layer using a nitrogen-based plasma, and removing the exposed portion of the middle layer using a wet strip process, wherein damage to the lower layer is minimized due to the plasma treatment, as claimed in claim 12; and d) applying a nitrogen plasma treatment to at least a portion of the etch stop layer, and removing the treated portion of the etch stop layer to expose a portion of the underlying metal silicide layer, wherein the plasma treatment reduces damage to the

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underlying metal silicide layer that occurs during the removing of the treated portion of

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the etch stop layer, as claimed in claim 18.

3. Any comments considered necessary by applicant must be submitted no later than the

payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Allowance."

4. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Luan Thai whose telephone number is 571-272-1935. The

examiner can normally be reached on 6:45 AM - 4:15 PM, Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Michael Tokar can be reached on 571-272-1812. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Luan Thai

Primary Examiner Art Unit 2829

December 9, 2004